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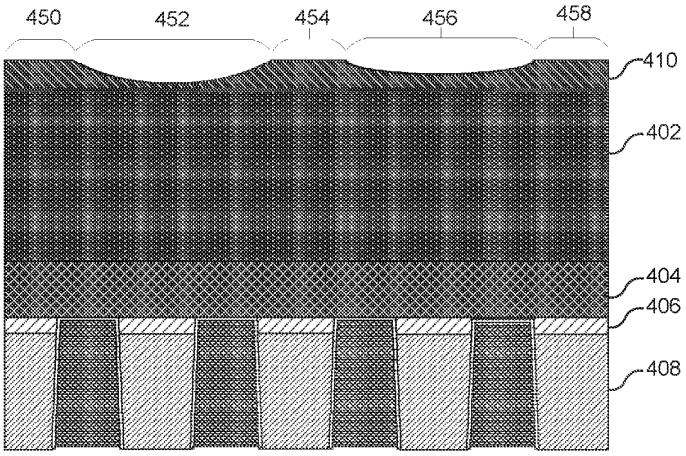

FIG. 4G

(57) Abstract: A semiconductor structure including a dielectric film wherein stress has been inducted into one or more stressed portions of the dielectric film to create one or more stress zones. The stress zones correspond to locations of warpage in the semiconductor structure and reduce warpage. In some examples, the stress zones can be created by exposing portions of the dielectric film to different amounts of heat. In some examples, the stress zones can be created by one or more recesses in the dielectric film.

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